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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/702,615	11/07/2003	In Duk Song	8733.930.00-US	8495	
30827	7590 10/04/2006		EXAM	EXAMINER	
MCKENNA LONG & ALDRIDGE LLP			KIM, RIC	KIM, RICHARD H	
1900 K STREI WASHINGTO	EI, NW DN, DC 20006		ART UNIT	ART UNIT PAPER NUMBER	
	,		2871		
			DATE MAILED: 10/04/200	DATE MAILED: 10/04/2006	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/702,615	SONG ET AL.				
Office Action Summary	Examiner	Art Unit				
	Richard H. Kim	2871				
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with	the correspondence ad	ldress			
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DATE of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period vortice and the second period for reply within the set or extended period for reply will, by statute any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICA 36(a). In no event, however, may a repl will apply and will expire SIX (6) MONTH , cause the application to become ABAN	ATION. y be timely filed IS from the mailing date of this countries IDONED (35 U.S.C. § 133).				
Status						
1)⊠ Responsive to communication(s) filed on 17 Ju	ılv 2006					
· · · · · · · · · · · · · · · · · · ·	action is non-final.					
)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the ments is						
closed in accordance with the practice under E	•	•	, memo is			
Disposition of Claims	, , , , , , , , , , , , , , , , , , , ,					
4)⊠ Claim(s) <u>1,3-9,11 and 12</u> is/are pending in the	annlication	•				
	4a) Of the above claim(s) <u>5-8</u> is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.	nom consideration.	•				
6) Claim(s) <u>1,3,4,9,11 and 12</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or	r election requirement.					
Application Papers						
	_					
9) The specification is objected to by the Examine		the Evenines				
10) The drawing(s) filed on is/are: a) acce						
Applicant may not request that any objection to the			TD 4 404(4)			
Replacement drawing sheet(s) including the correction 11) The oath or declaration is objected to by the Ex						
	ammer. Note the attached C	Ance Action of John P1	U-152.			
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 1	19(a)-(d) or (f).				
a) ☐ All b) ☐ Some * c) ☐ None of:						
1. Certified copies of the priority documents						
2. Certified copies of the priority documents						
Copies of the certified copies of the prior		ceived in this National	Stage			
application from the International Bureau	, ,,,					
* See the attached detailed Office action for a list of	of the certified copies not re	ceived.				
Attachment(s)						
Notice of References Cited (PTO-892)	4) 🔲 Interview Sum					
2)		fail Date mal Patent Application				
Paper No(s)/Mail Date <u>7/17/06</u> .	6) Other:	ты атент Аррисацоп				

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 7/17/06 has been entered.

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1, 2, 4, 9, 10 and 12 rejected under 35 U.S.C. 102(b) as being anticipated by Ono et al. (US 6,726,802 B2).

As to claim 1, Ono et al. discloses a plurality of gate lines aligned on the substrate, a plurality of data lines crossing the gate lines to form a plurality of pixel regions (Fig. 19, ref. GL, DL); a thin film transistor located at the intersection of a gate line and a data line (TFT); a pixel electrode located in each pixel region (Fig. 21, ref. PIX (ITO1)), wherein the array substrate includes a storage capacitor comprising a lower storage electrode across the data line and in parallel with the gate line on the same layer as the gate line (Fig. 21, ref. CT(g1); col. 21, lines

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14-15), wherein the lower storage electrode divides the pixel region into two sub-regions (Fig. 19, ref. CT(g1)), and a semiconductor layer interposed between the lower storage electrode and the pixel electrode (Fig. 21, ref. AS), wherein the pixel electrode is connected to the semiconductor layer by a through hole formed on an upper region of the semiconductor layer (Fig. 21, ref. AS, PX(ITO1)). As shown if figure 21, there is a remaining portion of the pixel electrode above the storage capacitor. Therefore, the storage capacitor divides the pixel electrode into two sub-regions (region of the pixel electrode above the storage capacitor and region of the pixel electrode below the storage capacitor).

Referring to claim 4, Ono et al. discloses that only the semiconductor layer and a gateinsulating layer are interposed between the lower storage electrode and the pixel electrode (Fig. 21, ref. GI, AS).

Referring to claim 9, Ono et al. discloses a gate line (GL), a gate electrode (GL), and a lower storage capacitor (Cstg); an insulating layer (GI) on the substrate having the gate line, gate electrode, and lower storage electrode, a semiconductor layer (AS) on the lower storage electrode, a data line (DL) on the substrate having the insulating layer; a protection layer (PSV2) on the substrate having the data line, the protection layer having a through hole (CN) above a part of the semiconductor layer, and a pixel electrode (PX) on the protection layer, wherein the pixel electrode contacts the top of the semiconductor layer, wherein the gate line and data line cross to form a pixel region; and wherein the storage electrode is parallel to the gate line and divides the pixel region into two sub-regions (Fig. 21, ref. CL), and wherein the pixel electrode is connected to the semiconductor layer by the through hole above the semiconductor layer (Fig. 21, ref. AS, PX(ITO1)).

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Referring to claim 12, Ono et al. disclose that only the semiconductor layer and a gate-insulating layer are interposed between the lower storage electrode and the pixel electrode (Fig. 21, ref. GI, AS).

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claim 3 and 11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ono et al.

Ono et al. discloses the device previously recited, and further discloses that the semiconductor layer is inside the pixel region (Fig. 21, ref. AS). However, the reference fails to disclose that the semiconductor layer is at least as wide as the lower storage electrode.

It would have been obvious to one having ordinary skill in the art at the time the invention was made for the semiconductor region to be at least as wide as the lower storage electrode since Ono et al. discloses that the semiconductor layer increases the charge holding capacitance value per area (col. 24, lines 24-25). Therefore, increasing the width, in order to increase the charge holding capacitance is a result effective variable and requires only routine skill in the art.

Response to Arguments

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5. Applicant's arguments filed 7/17/06 have been fully considered but they are not persuasive.

6. In response to Applicant's argument that since Figs. 17 and 21 pertain to different embodiment of the invention and therefore a proper rejection cannot be made, Examiner agrees that Figs. 17 and 21 pertain to different embodiment. However, the claimed limitations can be rejected using solely Figure 21.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard H. Kim whose telephone number is (571)272-2294. The examiner can normally be reached on 9:00-6:30 M-F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571)272-1787. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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Richard H Kim Examiner Art Unit 2871

RHK

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ANDREW SCHECHTER PRIMARY EXAMINER